

isc Silicon PNP Power Transistor

2SB1273

DESCRIPTION

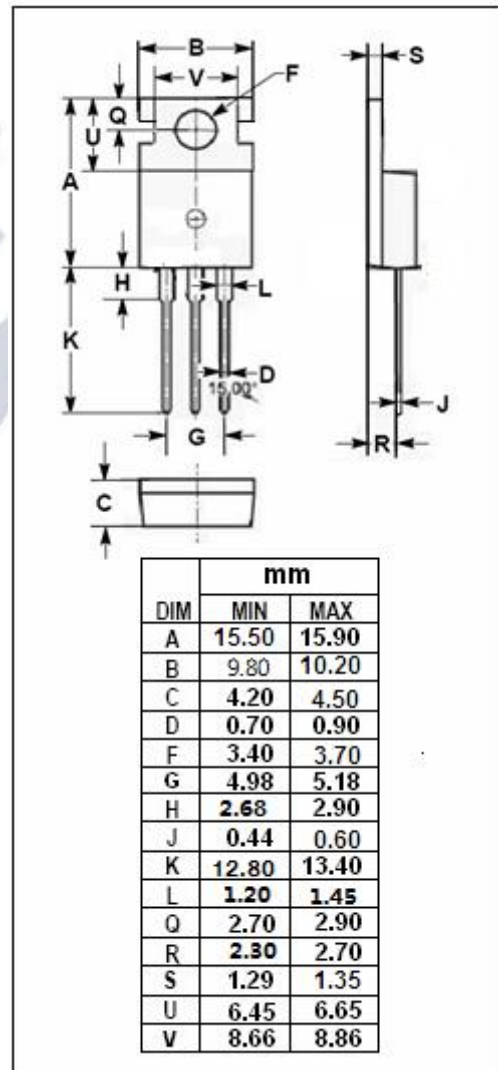
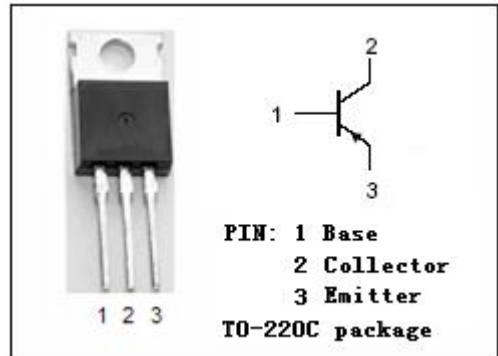
- High Reliability
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -1.0V(\text{Max}) @ I_C = -2A$
- Wide Area of Safe Operation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-8	A
P_C	Total Power Dissipation @ $T_a=25^\circ\text{C}$	1.75	W
	Total Power Dissipation @ $T_c=25^\circ\text{C}$	30	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA; R _{BE} = ∞	-60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -0.5A; V _{CE} = -5V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -40V; I _E = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -5V	70		280	
h _{FE-2}	DC Current Gain	I _C = -3A; V _{CE} = -5V	20			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		60		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -5V		100		MHz

◆ **h_{FE-1} Classifications**

Q	R	S
70-140	100-200	140-280